/ Descriptions

TO-277

TO-277 Plastic package Ultrafast Recovery Diode.

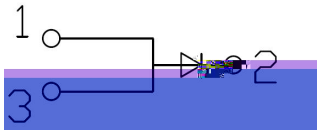
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability. HF Product.

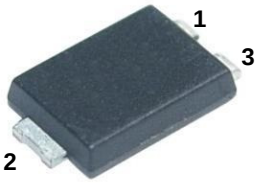
/ Applications

For use in low voltage,high frequency inverters, free wheeling, and polarity protection applications.

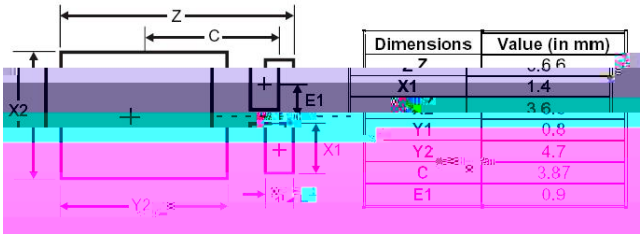
/ Equivalent Circuit



/ Pinning



PIN1 Anode PIN 2 Cathode PIN 3 Anode



Suggested Pad layout

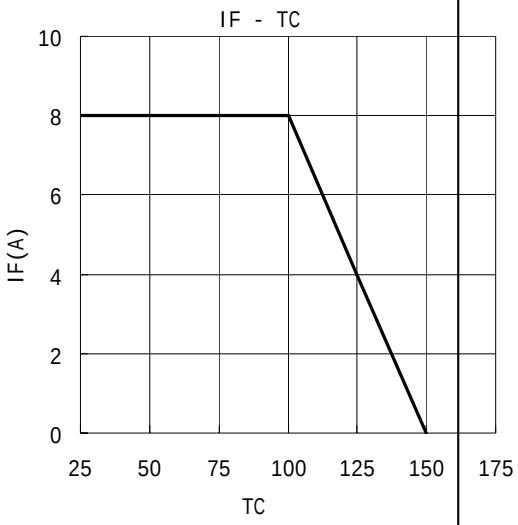
/ h_{FE} Classifications & Marking

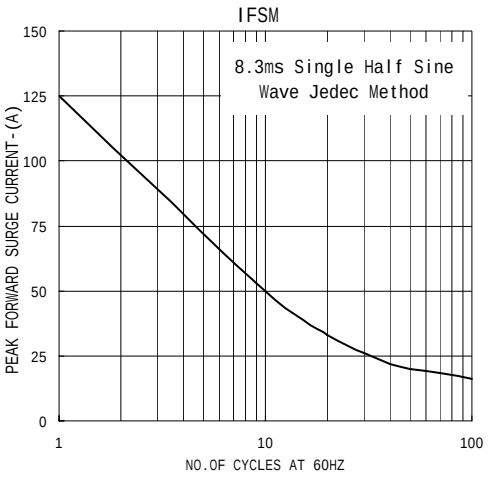
See Marking Instructions.

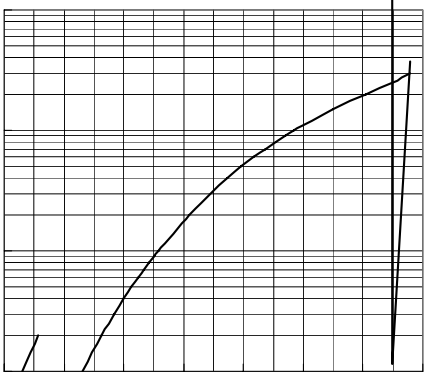
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Reverse voltage	V_{RMS}	420	V
Average Rectified Forward Current	I_F	8	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	125	A
Thermal Resistance Junction to Case	$R_{\theta Jc}$	3.5	/W
Junction and Storage Temperature Range	T_j T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_{BR}	I_R=100uA	600			V
Forward voltage	V_F	I_F=8A Tc=25		1.4	1.7	V
		I_F=16A Tc=25		1.7	2.1	V
		I_F=8A Tc=125		1.4	1.7	V
Instantaneous Reverse Current	I_R Note 1	V_R=600V Ta=25			5	uA
		V_R=480V Ta=125			300	uA
		V_R=600V Ta=125			500	uA

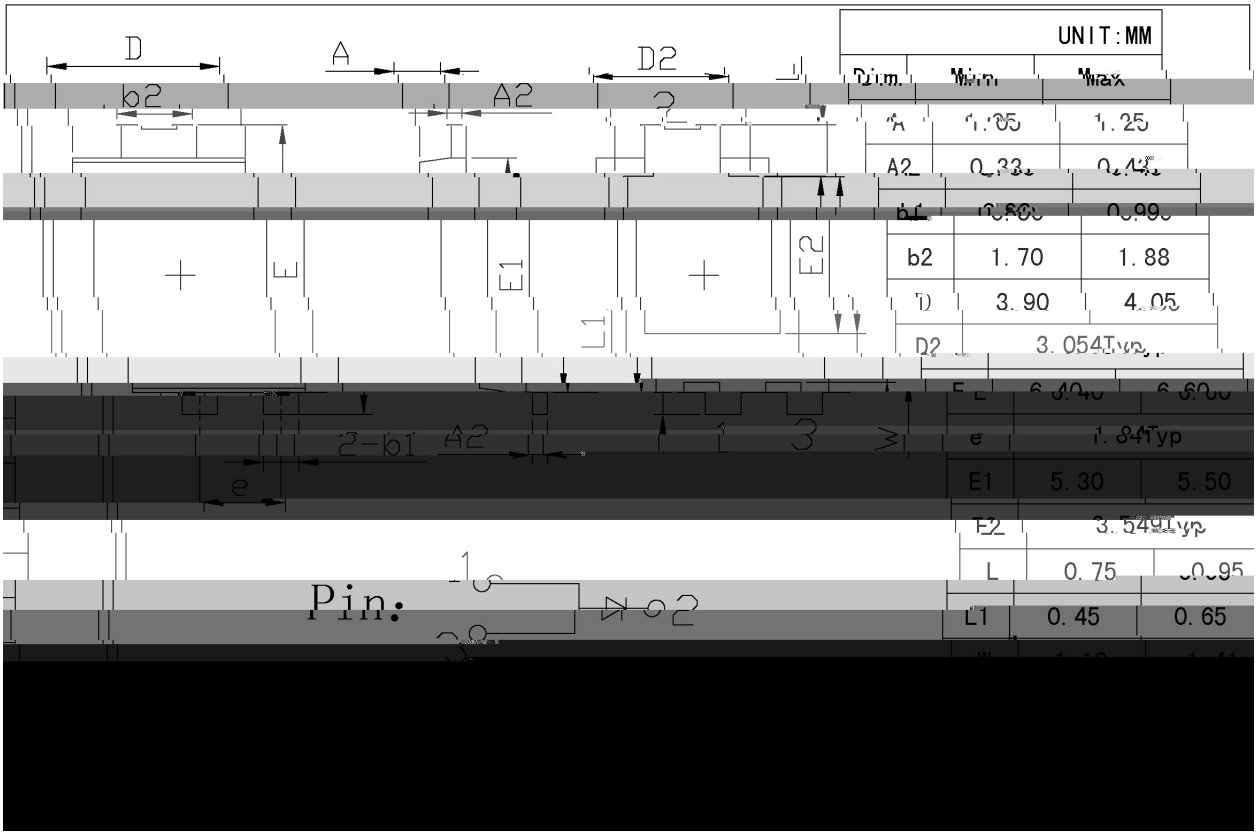
/ Electrical Characteristic Curve







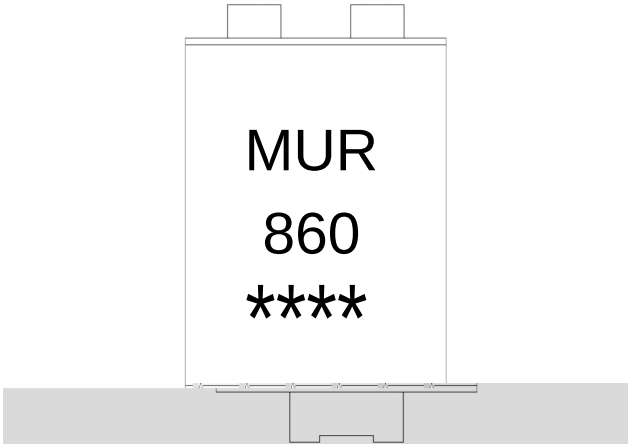
/ Package Dimensions



UNIT:MM

Dim.	Min.	Max.
A	1.05	1.25
A2	0.33	0.43
b1	0.80	0.99
b2	1.70	1.88
D	3.90	4.05
D2	3.054Typ.	
E	6.40	6.60
e	1.84Typ	
E1	5.30	5.50
E2	3.549Typ	
L	0.75	0.95
L1	0.45	0.65

/ Marking Instructions



MUR860
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Note:

MUR860	Product Type.
****:	Lot No. Code, code change with Lot No.